

# **Phase Control Thyristor**

DS6025-2 December 2013 (LN31165)

#### **FEATURES**

- Double Side Cooling
- High Surge Capability

## **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

#### **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages V <sub>DRM</sub> and V <sub>RRM</sub> V	Conditions
DCR720E18 DCR720E16 DCR720E14 DCR720E12	1800 1600 1400 1200	$\begin{split} T_{vj} = -40^{\circ}\text{C to } 125^{\circ}\text{C}, \\ I_{DRM} = I_{RRM} = 30\text{mA}, \\ V_{DRM}, V_{RRM}  t_p = 10\text{ms}, \\ V_{DSM}  \&  V_{RSM} = \\ V_{DRM}  \&  V_{RRM}  +100V \\ respectively \end{split}$

Lower voltage grades available.

#### **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

#### **DCR720E18**

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

#### **KEY PARAMETERS**

$V_{DRM}$	1800 V
$I_{T(AV)}$	720 A
I <sub>TSM</sub>	8300 A
dV/dt*	1000 V/µs
dI/dt	200 A/μs

#### \* Higher dV/dt selections available

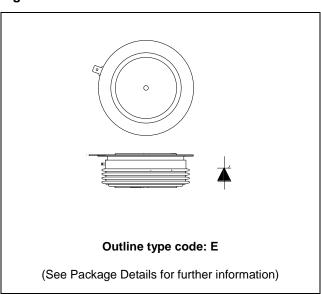


Fig. 1 Package outline



## **CURRENT RATINGS**

## $T_{\text{case}}$ = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions		Units
Double Si	de Cooled			
I <sub>T(AV)</sub>	Mean on-state current	Half wave resistive load	720	А
I <sub>T(RMS)</sub>	RMS value	-	1220	А
I <sub>T</sub>	Continuous (direct) on-state current	-	1100	Α

## **SURGE RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125$ °C	8.3	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$V_R = 0$	0.344	MA <sup>2</sup> s

# THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions	5	Min.	Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance – junction to case	Double side cooled	DC		0.041	°C/W
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink	Double side cooled	DC		0.01	°C/W
$T_{vj}$	Virtual junction temperature	Blocking V <sub>DRM</sub> / V <sub>RRM</sub>			125	°C
T <sub>stg</sub>	Storage temperature range			-40	140	°C
F <sub>m</sub>	Clamping force			4	6	kN



# **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C		-	30	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% $V_{DRM}$ , $T_j = 125$ °C, ga	To 67% V <sub>DRM</sub> , T <sub>j</sub> = 125°C, gate open		-	V/µs
dl/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 1000A	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	1000	A/µs
		$t_r < 0.5 \mu s, T_j = 125 ^{\circ} C$				
$V_{T}$	On-state voltage	IT = 1500A, T <sub>case</sub> = 125°C			1.97	٧
V <sub>T(TO)</sub>	Threshold voltage – Low level	T <sub>case</sub> = 125°C		-	1.09	V
r <sub>T</sub>	On-state slope resistance – Low level	T <sub>case</sub> = 125°C		-	0.587	mΩ
t <sub>gd</sub>	Delay time	$V_D = 67\% \ V_{DRM}$ , gate source 30V, $10\Omega$		-	3.0	μs
	,	$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
$t_{q}$	Turn-off time	$T_j = 125$ °C, $V_R = 100$ V, $dI/dt = 10$ A/ $\mu$ s,		-	150	μs
		$dV_{DR}/dt = 20V/\mu s$ linear to 67% $V_{DRM}$				
Qs	Stored charge	$I_T = 1000A$ , tp = 1000us, $T_j = 125$ °C, dl/dt =10A/µs,		-	1500	μC
I <sub>RR</sub>	Reverse recovery current			-	110	Α
lι	Latching current	$T_j = 25$ °C,		-	1	Α
l <sub>Η</sub>	Holding current	T <sub>j</sub> = 25°C,		-	200	mA

# **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
$V_{GT}$	Gate trigger voltage	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	3	V
$V_{GD}$	Gate non-trigger voltage	At 40% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	TBD	V
I <sub>GT</sub>	Gate trigger current	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	300	mA
I <sub>GD</sub>	Gate non-trigger current	At 40% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	TBD	mA



#### **CURVES**

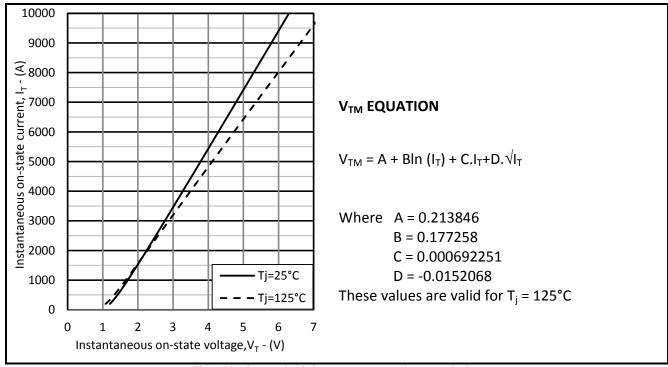


Fig.2 Maximum &minimum on-state characteristics

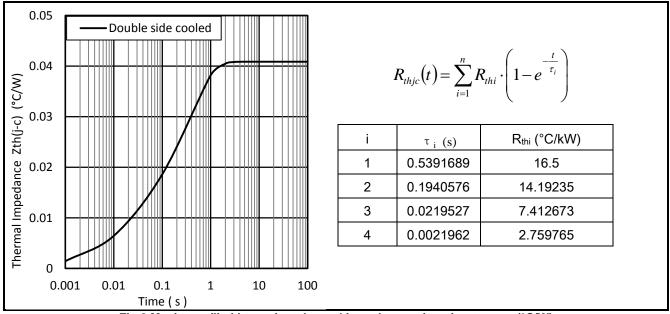
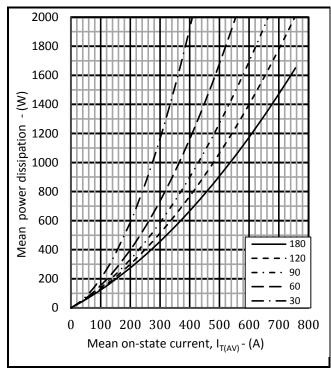


Fig.3 Maximum (limit) transient thermal impedance – junction to case (°C/W)







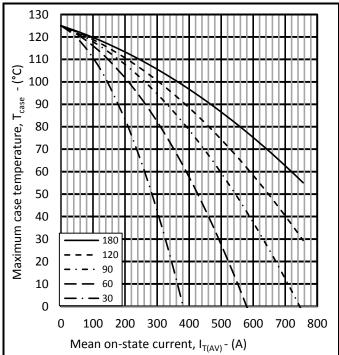


Fig.5 Maximum permissible case temperature, double side cooled – sine wave

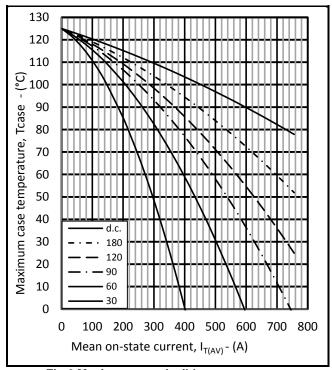


Fig.6 Maximum permissible case temperature, double side cooled – rectangular wave

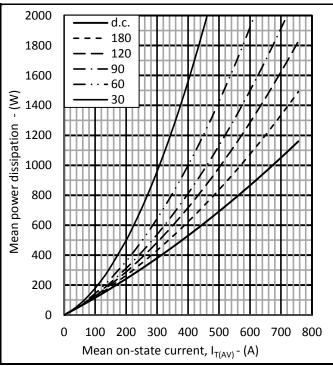
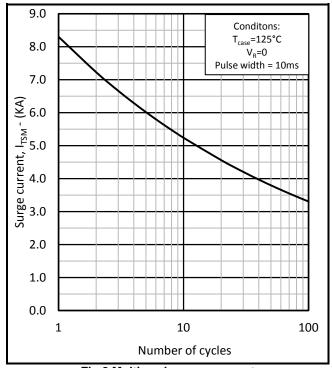
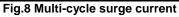


Fig.7 On-state power dissipation - rectangular wave







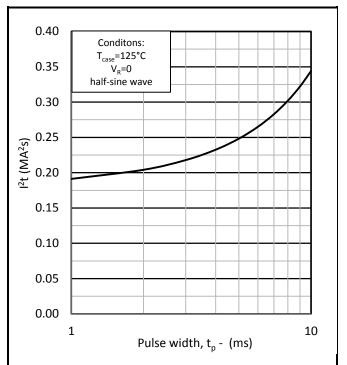


Fig.9 Single-cycle I2t

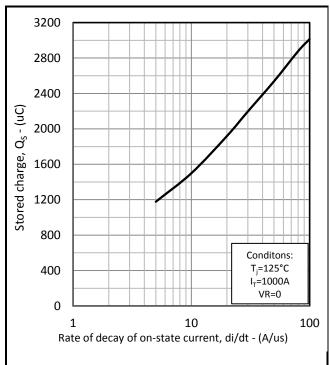


Fig.10 Stored charge vs di/dt

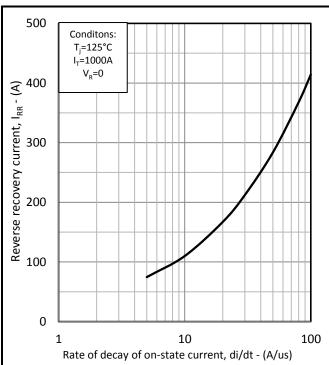


Fig.11 Reverse recovery current vs di/dt



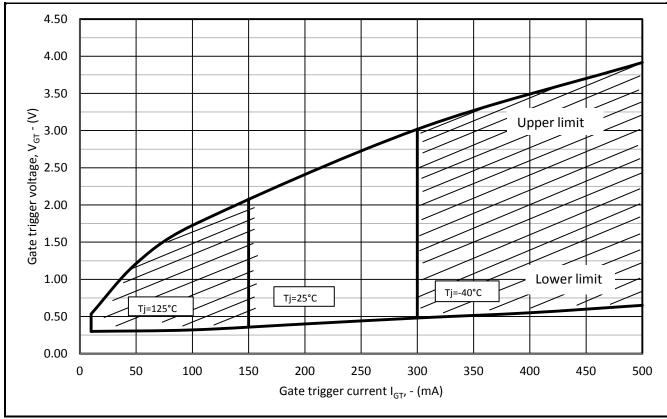


Fig.12 Gate characteristics

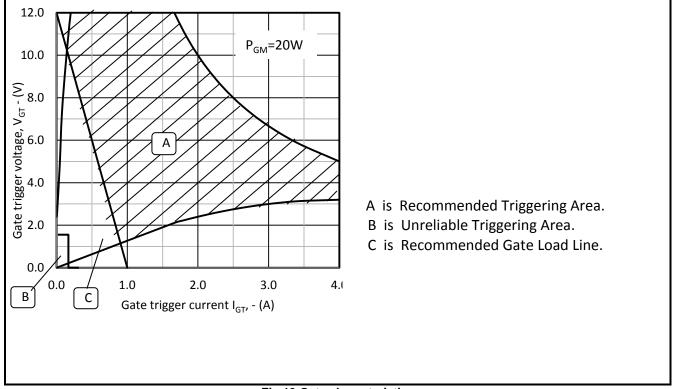


Fig.13 Gate characteristics



## **PACKAGE DETAILS**

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

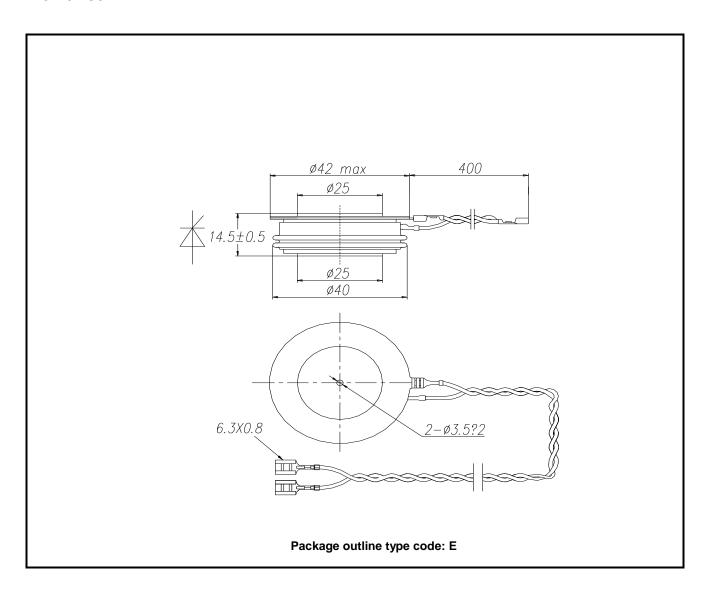


Fig.14 Package outline



#### IMPORTANT INFORMATION:

This publication is provided for information only and not for resale.

The products and information in this publication are intended for use by appropriately trained technical personnel.

Due to the diversity of product applications, the information contained herein is provided as a general guide only and does not constitute any guarantee of suitability for use in a specific application. The user must evaluate the suitability of the product and the completeness of the product data for the application. The user is responsible for product selection and ensuring all safety and any warning requirements are met. Should additional product information be needed please contact Customer Service.

Although we have endeavoured to carefully compile the information in this publication it may contain inaccuracies or typographical errors. The information is provided without any warranty or guarantee of any kind.

This publication is an uncontrolled document and is subject to change without notice. When referring to it please ensure that it is the most up to date version and has not been superseded.

The products are not intended for use in applications where a failure or malfunction may cause loss of life, injury or damage to property. The user must ensure that appropriate safety precautions are taken to prevent or mitigate the consequences of a product failure or malfunction.

The products must not be touched when operating because there is a danger of electrocution or severe burning. Always use protective safety equipment such as appropriate shields for the product and wear safety glasses. Even when disconnected any electric charge remaining in the product must be discharged and allowed to cool before safe handling using protective gloves.

Extended exposure to conditions outside the product ratings may affect reliability leading to premature product failure. Use outside the product ratings is likely to cause permanent damage to the product. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture, a large current to flow or high voltage arcing, resulting in fire or explosion. Appropriate application design and safety precautions should always be followed to protect persons and property.

#### **Product Status & Product Ordering:**

We annotate datasheets in the top right hand corner of the front page, to indicate product status if it is not yet fully approved for production. The annotations are as follows:-

Target Information: This is the most tentative form of information and represents a very preliminary specification.

No actual design work on the product has been started.

Preliminary Information:

The product design is complete and final characterisation for volume production is in

progress. The datasheet represents the product as it is now understood but details may change. The product has been approved for production and unless otherwise notified by Dynex any product ordered will be supplied to the current version of the data sheet prevailing at the

time of our order acknowledgement.

All products and materials are sold and services provided subject to Dynex's conditions of sale, which are available on request.

Any brand names and product names used in this publication are trademarks, registered trademarks or trade names of their respective owners.

#### **HEADQUARTERS OPERATIONS**

DYNEX SEMICONDUCTOR LIMITED
Doddington Road, Lincoln, Lincolnshire, LN6 3LF

United Kingdom.

No Annotation:

Phone: +44 (0) 1522 500500 Fax: +44 (0) 1522 500550 Web: http://www.dynexsemi.com

#### **CUSTOMER SERVICE**

Phone: +44 (0) 1522 502753 / 502901 Fax: +44 (0) 1522 500020 e-mail: power\_solutions@dynexsemi.com

© Dynex Semiconductor Ltd. Technical Documentation – Not for resale.